AMT1225 1 – 18GHz Low Noise Amplifier Chip

Key Features:

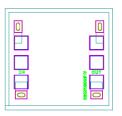
Frequency range: 1 – 18GHz
Typical gain: 15dB @ 38mA
Input standing wave: 1.5
Output standing wave: 1.4

• Noise figure: 1.8dB

P-1: 17dBm @ +5V/38mA

• Chip dimensions: 1.5mm x 0.95mm x 0.1mm

• Applications: wireless communication, transceiver module, radio telecommunication etc.



Description:

AMT1225 chip is a Gallium Arsenide (GaAs) high performance Low Noise Amplifier, it covers 1 – 18GHz frequency range. It uses +5V single voltage operation, noise figure is 1.8dB, and 15dB typical gain. This chip is designed with ground through metal vias on the back technology.

Absolute Maximum Ratings (Ta = 25°C)

Symbol	Parameter	Value	Remark
Vd	Drain Voltage	+7V	
Pin	Input Signal Power	17dBm	
Tch	Operating Temperature	150°C	
Tm	Sintering Temperature	310°C	30s, N ₂ protection
Tstg	Storage Temperature	-65 ~ +150°C	

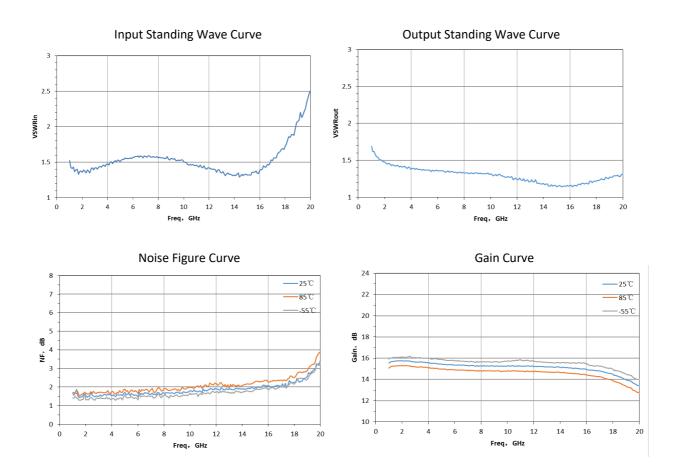
[1] Operation outside any of the Absolute Maximum Ratings may cause permanent device damage.

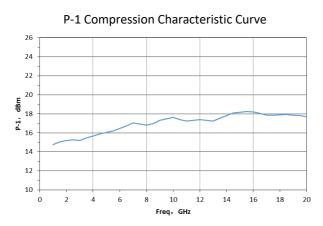
Electrical Characteristics (Ta = 25°C)

Symbol	Parameter	Test Conditions	Value			Unit
			Min	Typical	Max	
G	Gain		-	15	-	dB
NF	Noise Figure		-	1.8	-	dB
Id	Static Current	Vd = +5V	-	38	-	mA
VSWR_in	Input Standing Wave	F : 1 ~ 18GHz	-	1.5	-	-
VSWR_out	Output Standing Wave		-	1.4	-	-
P-1	Output Power at 1dB point		-	17	-	dBm

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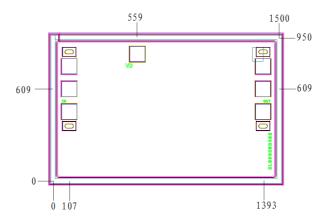
Typical Performance



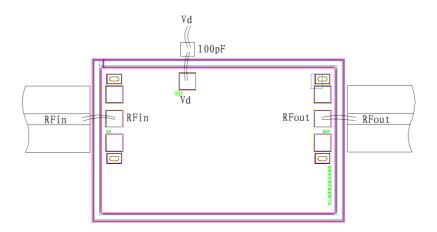


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Chip Dimensions (Unit: µm)



Chip Layout Diagram



Pad Definition

Symbol	Function Description	Demensions	Equivalent Circuit
RFin	RF signal input port, connecting to external 50 Ω system, need to add DC blocking capacitor.	100μm*100μm	RF-in
RFout	RF signal output port, connecting to external 50 Ω system, need to add DC blocking capacitor.	100μm*100μm	RF-out
VD	Amplifier bias, need to connect 100pF external capacitor	100μm*100μm	VD The state of th

Please see Appendix A for details.